

Features

- High current capability
- Avalanche rated
- Low forward voltage drop
- High frequency operation

Description

This Schottky diode is suited for high frequency switch mode power supply.

Packaged in TO-220AB narrow leads and I²PAK, this device is intended to be used in notebook, game station and desktop adapters, providing in these applications a good efficiency at both low and high load.

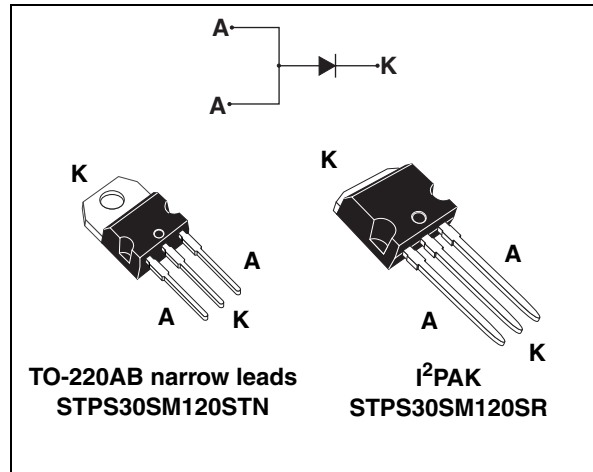


Figure 1. Electrical characteristics^(a)

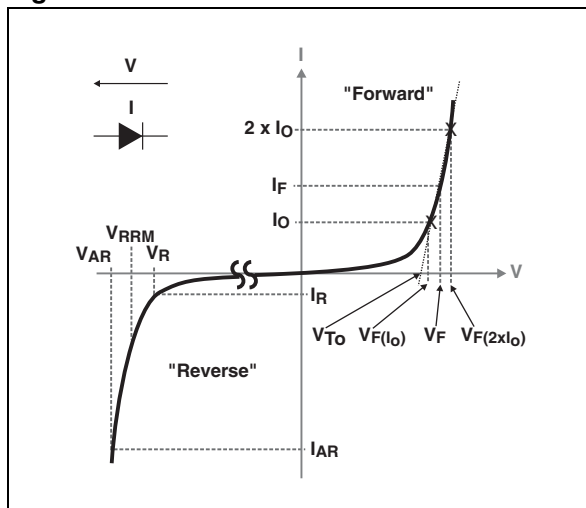


Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	30 A
V_{RRM}	120 V
$T_j \text{ (max)}$	150 °C
$V_F \text{ (typ)}$	0.47 V

- a. V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in [Figure 9](#). V_{AR} and I_{AR} are pulse measurements ($t_p < 10 \mu s$). V_R , I_R , V_{RRM} and V_F are static characteristics

1 Characteristics

Table 2. Absolute ratings (limiting values with terminals 1 and 3 short circuited at $T_{amb} = 25\text{ °C}$, unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	120	V
$I_{F(RMS)}$	Forward rms current	50	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_c = 110\text{ °C}$	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms sine-wave}$	A
$P_{ARM}^{(1)}$	Repetitive peak avalanche power	$T_j = 125\text{ °C}, t_p = 10\text{ }\mu\text{s}$	W
$V_{ARM}^{(2)}$	Maximum repetitive peak avalanche voltage	$t_p < 10\text{ }\mu\text{s}, T_j < 125\text{ °C}, I_{AR} < 8\text{ A}$	V
$V_{ASM}^{(2)}$	Maximum single-pulse peak avalanche voltage	$t_p < 10\text{ }\mu\text{s}, T_j < 125\text{ °C}, I_{AR} < 8\text{ A}$	V
T_{stg}	Storage temperature range	-65 to +175	°C
T_j	Maximum operating junction temperature ⁽³⁾	150	°C

1. For pulse time duration deratings, please refer to [Figure 4](#). More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the STMicroelectronics Application notes AN1768, "Admissible avalanche power of schottky diodes" and AN2025, "Converter improvement using Schottky rectifier avalanche specification".

2. See [Figure 9](#)

3. $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	1.35	°C/W

Table 4. Static electrical characteristics (terminals 1 and 3 short circuited)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	-	55	275	μA
		$T_j = 125\text{ °C}$	-	20	50	mA
$V_F^{(2)}$	Forward voltage drop	$T_j = 125\text{ °C}$	$I_F = 5\text{ A}$	-	0.47	0.52
		$T_j = 125\text{ °C}$	$I_F = 10\text{ A}$	-	0.55	0.60
		$T_j = 25\text{ °C}$	$I_F = 15\text{ A}$	-		0.79
		$T_j = 125\text{ °C}$		-	0.60	0.65
		$T_j = 25\text{ °C}$	$I_F = 30\text{ A}$	-		0.95
		$T_j = 125\text{ °C}$		-	0.68	0.76

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$

2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.56 \times I_{F(AV)} + 0.0067 \times I_{F(RMS)}^2$$

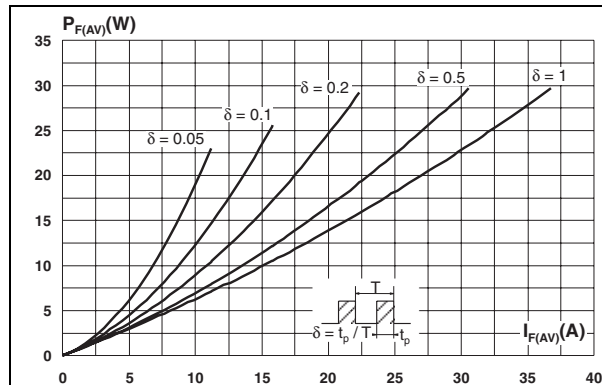
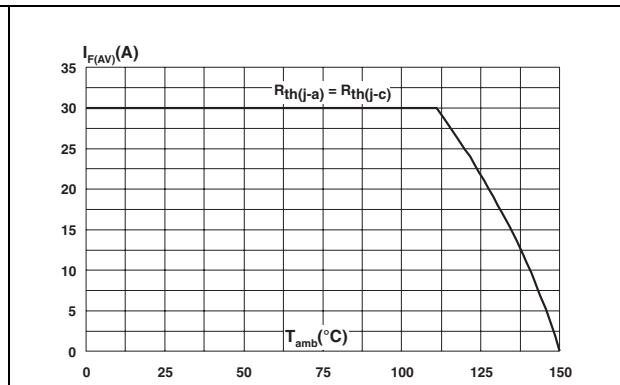
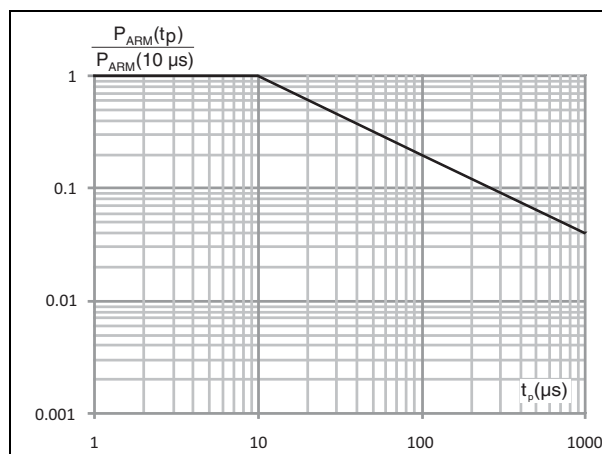
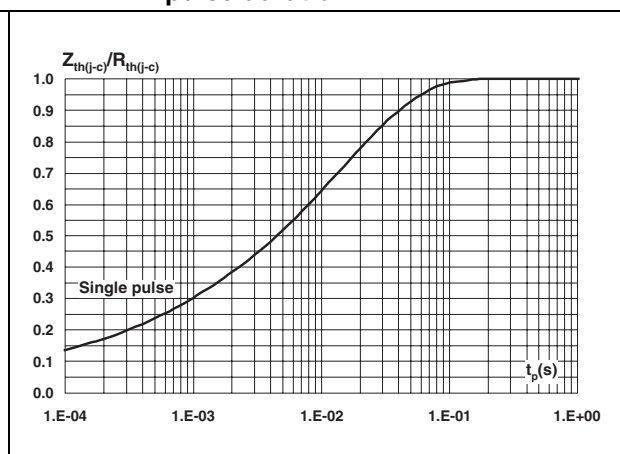
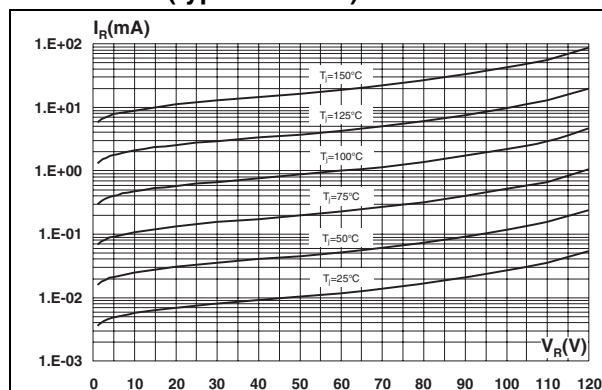
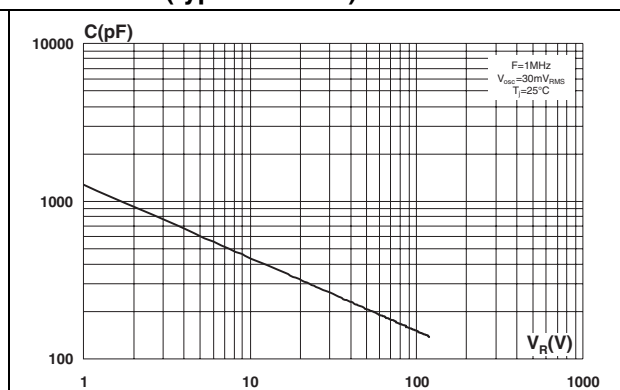
Figure 2. Average forward power dissipation versus average forward current**Figure 3. Average forward current versus ambient temperature ($\delta = 0.5$)****Figure 4. Normalized avalanche power derating versus pulse duration****Figure 5. Relative variation of thermal impedance junction to case versus pulse duration****Figure 6. Reverse leakage current versus reverse voltage applied (typical values)****Figure 7. Junction capacitance versus reverse voltage applied (typical values)**

Figure 8. Forward voltage drop versus forward current

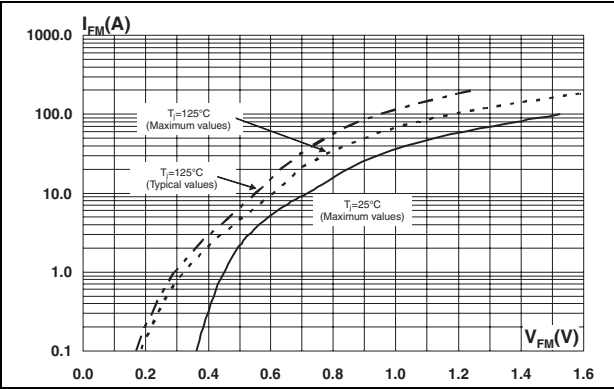
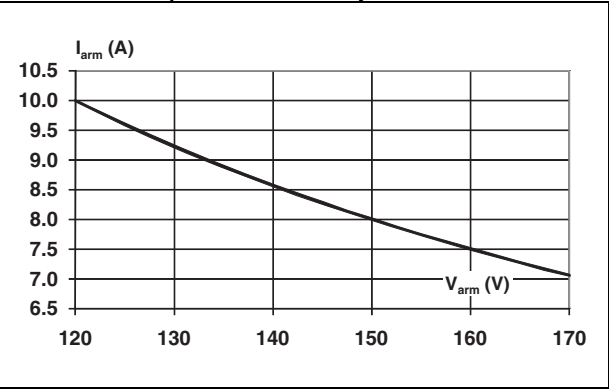


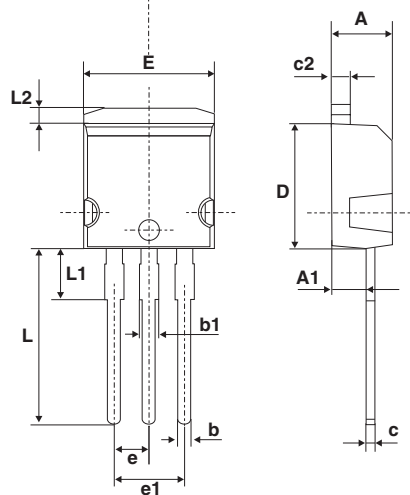
Figure 9. Reverse safe operating area ($t_p < 10\ \mu\text{s}$ and $T_j < 125^\circ\text{C}$)



Devices in I²PAK with nickel-plated back frame must NOT be mounted by frame soldering like SMDs. Such devices are intended to be through-hole mounted ONLY and in no circumstances shall ST be held liable for any lack of performance or damage arising out of soldering of nickel-plated back frames.

Table 6. I²PAK dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
c	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
E	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055



3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS30SM120SR	PS30SM120SR	I ² PAK	1.49 g	50	Tube
STPS30SM120STN	PS30SM120STN	TO-220AB narrow leads	1.9 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
02-Apr-2012	1	First issue.

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